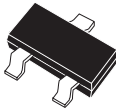


## CMPD914

### HIGH SPEED SWITCHING DIODE



**SOT-23 CASE**

### DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPD914 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.

**Marking code is C5D.**

### MAXIMUM RATINGS (T<sub>A</sub>=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V <sub>R</sub>	75	V
Peak Repetitive Reverse Voltage	V <sub>R</sub> RM	100	V
Continuous Forward Current	I <sub>F</sub>	250	mA
Peak Repetitive Forward Current	I <sub>F</sub> RM	250	mA
Forward Surge Current, tp=1 μsec.	I <sub>F</sub> SM	4000	mA
Forward Surge Current, tp=1 msec.	I <sub>F</sub> SM	2000	mA
Forward Surge Current, tp=1 sec.	I <sub>F</sub> SM	1000	mA
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	Θ <sub>JA</sub>	357	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V <sub>BR</sub>	I <sub>R</sub> =100μA	100		V
I <sub>R</sub>	V <sub>R</sub> =20V		25	nA
I <sub>R</sub>	V <sub>R</sub> =75V		5.0	μA
V <sub>F</sub>	I <sub>F</sub> =10mA		1.0	V
C <sub>T</sub>	V <sub>R</sub> =0, f=1 MHz		4.0	pF
t <sub>rr</sub>	I <sub>R</sub> =I <sub>F</sub> =10mA, R <sub>L</sub> =100Ω, Rec. to 1.0mA		4.0	ns

All dimensions in inches (mm).

